MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet





TRANSISTOR (PNP)

FEATURES

Low Speed Switching

TO-252-2L

- 1. BASE
- 2. COLLECTOR
- 3 .EMITTER

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

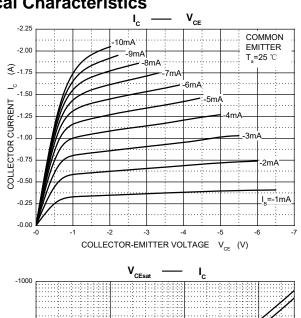
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-6	V
Ic	Collector Current -Continuous	-3	Α
Pc	Collector Power Dissipation	1.25	W
R _{OJA}	Thermal Resistance, junction to Ambient	100	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

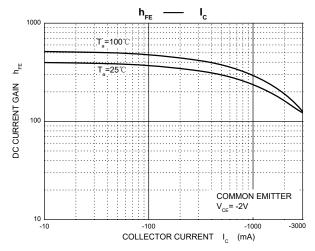
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

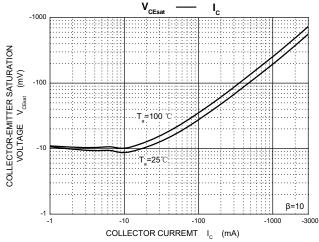
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA ,I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA , I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA,I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			-0.	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.	V
Transition frequency	f⊤	V_{CE} = -5V, I_{C} =-0.1A f =10MHz	50	8		MHz

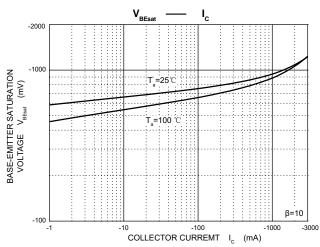


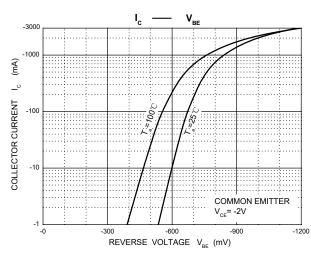
Typical Characteristics

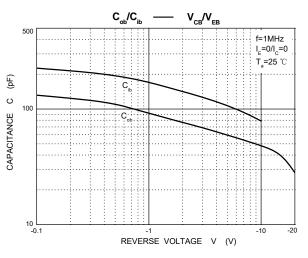


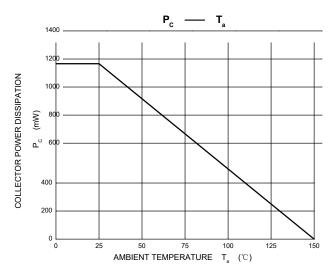






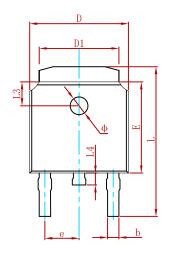


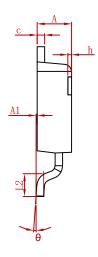


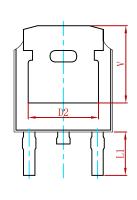




PACKAGE MECHANICAL DATA

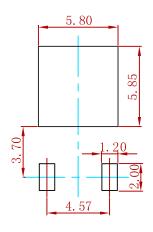






0	Dimensions In Millimeters Min. Max.		Dimensions In Inches		
Symbol			Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	REF.	0.190	REF.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900	REF.	0.114	REF.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063	REF.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SB772	TO-252	2500



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